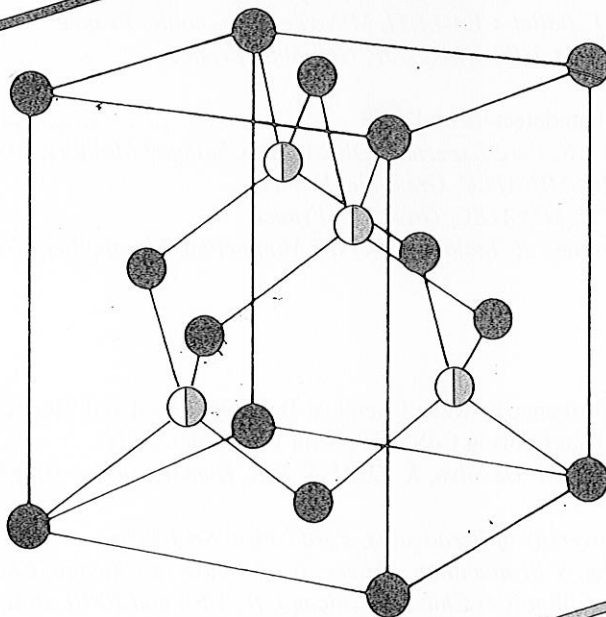


EXTENDED ABSTRACTS

THE 2013 U.S. WORKSHOP
on the PHYSICS and CHEMISTRY
of II-VI MATERIALS



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U.S. Army RDECOM CERDEC Night Vision &
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A comparison of performance between chemical bath deposited and electrochemical bath deposited CdS thin films in CdS/CdTe thin film solar cells

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Abstract

CdS thin films of about 60 nm thick were grown on appropriately cleaned, commercially available 2.3 mm thick, TEC 15 conducting glasses (1.5" x 1.5") using both, chemical bath deposition (CBD) and electrochemical bath deposition (ECBD) techniques. Close space sublimation (CSS) technique was used to deposit CdTe thin films of about 6 μm thick on both types of CdS layers. All TEC15/CdS/CdTe structures were heat treated with CdCl_2 , in inert environments. The following optimum performance characteristics were observed with initial, In/TEC 15/CdS/CdTe/Cu/Au devices made using the CdS thin films grown with both, CBD and ECBD processes.

Process	V_{oc} /(V)	J_{sc} /(mA cm ⁻²)	FF (%)	η (%)
CBD	0.814	25	71.3	14.5
ECBD	0.285	20.6	50.2	2.95

Key words: Chemical bath deposition (CBD), electrochemical bath deposition (ECBD), close space sublimation (CSS), CdS/CdTe thin film solar cell.

Introduction

CdS/CdTe thin film solar cells are one of the promising photovoltaic devices for low cost large area terrestrial applications.^[1-8] Highly efficient poly-crystalline CdS/CdTe cells have been fabricated by different techniques, viz. screen printing, close-spaced vapor transport, chemical bath deposition, electrochemical bath deposition, vacuum evaporation, chemical vapor deposition, etc. The deposition techniques and substrates used have been found to influence the resulting microstructure of the thin CdS films and the efficiency of the final solar cell. The chemical bath deposition (CBD) and electrochemical bath deposition (ECBD) techniques the two most extensively used inexpensive techniques.^[8,9,10]

Experimental

Chemical bath deposited CdS thin films were grown from alkaline solutions at 92°C, containing 0.0133 mol dm⁻³ cadmium acetate, 0.0266 mol dm⁻³ thiourea, and 4.0 mol dm⁻³ ammonium acetate each with a purity of 99.99 % or greater. About 37 minute of reaction time produced CdS layers of approximately 60 nm thick with n-type electrical conductivity.

A three electrode cell consisting of a working electrode and a counter electrode each of TEC 15 conducting glasses with a reference electrode of Ag(s)/AgCl(s)/Cl(aq) were used for the ECBD process. Cadmium chloride and ammonium thiosulfate each with a concentration of 0.0015 mol dm⁻³ and purity of 99 % were used as cadmium and sulfur precursors for all electrochemical depositions. CdS thin films were grown at a deposition voltage of -1100 mV with respect to the reference electrode. The pH of the solutions was 1.5 and the temperature was in the range of 28 to 30 °C. Solutions were moderately stirred during deposition and a film thickness of approximately 60 nm was obtained with a deposition time of about 60 minutes. All electrodeposited thin films of CdS were annealed at 400 °C in air for 10 minutes. Using UV visible absorption and transmission studies, the thicknesses and the band gaps of CdS thin films were estimated.

CdTe p- type thin films were grown on both chemical bath and electrochemical bath deposited CdS thin films using the close space sublimation (CSS) technique. Substrate and source temperatures used were 550 and 600 °C. Thin films of about 6 µm could be grown over 12 minute deposition time. All CdTe layers were annealed with CdCl₂ at 405 °C for 5 minutes. Cu based Au back contacts and indium front contacts were made on all TEC15/CdS/CdTe structures to fabricate initial solar cell devices and their subsequent electrical characterization.

Results & Discussion

Photo-electrochemical cell measurements indicated that, all electrochemical bath deposited CdS layers were of n-type in electrical conductivity. UV absorption and transmission studies showed that the band gaps of all CdS semiconductors and their thicknesses were ~2.40 eV and ~ 60 nm respectively.

Figure 1 indicates that among the initial solar cell devices fabricated the one with CdTe film thickness of 5.54 µm (CTC 377) has produced the highest efficiency of 14.5.

Figure 2 is a representation of variation of key performance characteristics of the devices with the thickness of the CdTe layer for the ECBD/CdS process. Among the 16 small devices, the device No C3, gave the highest efficiency 2.95 % and highest % fill factor of 50.

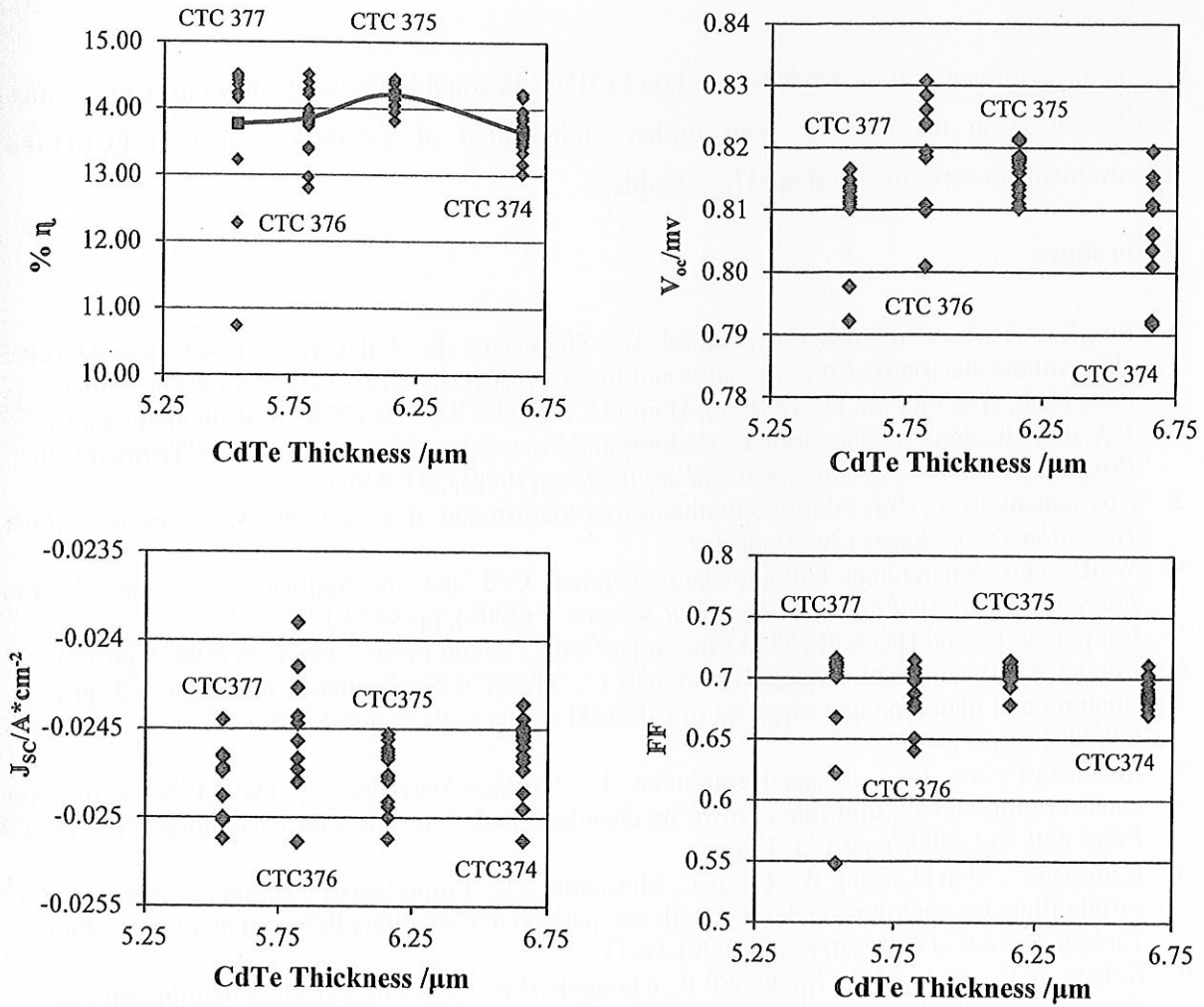


Figure 1: Variation of % Efficiency, V_{oc} , J_{sc} and Fill factor of CdS/CdTe semiconductor devices produced by CBD/CSS methods.

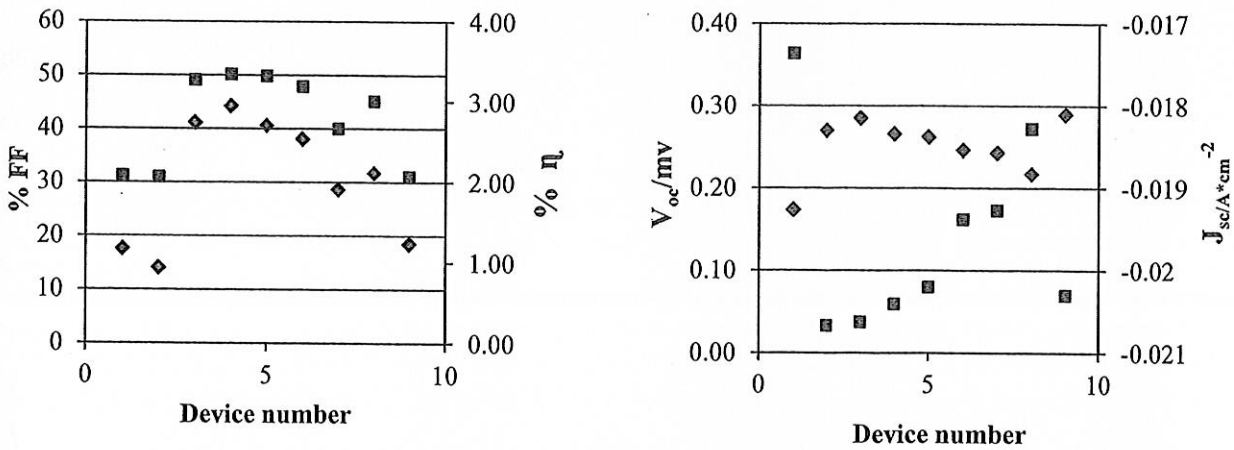


Figure 2: % Efficiency, V_{oc} , J_{sc} and Fill factor of CdS/CdTe semiconductor devices produced by ED/CSS methods

Conclusion

The poor performance of the devices based on ECBD/CdS could be due to the low purity of chemical and reagents used in the process. With further optimization of variables related to ECBD process improvements in performance should be possible.

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